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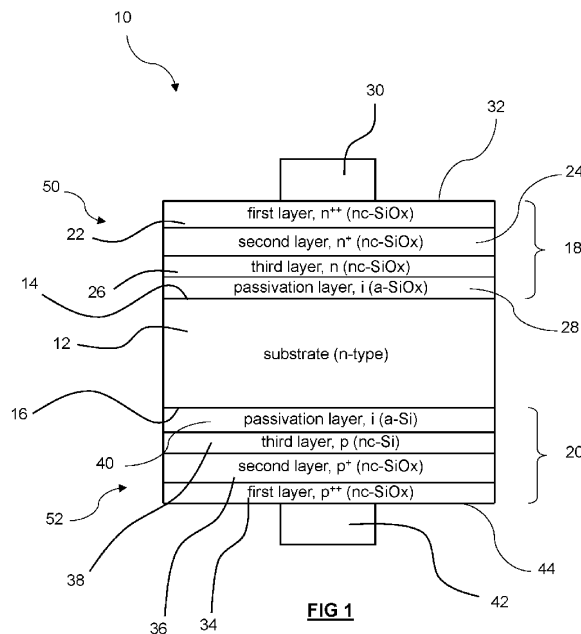


FIG 1

(57) Abstract: A solar cell comprising a silicon substrate and a layered structure arranged on a surface of the silicon substrate, the layered structure comprising; a first layer comprising a percentage of crystalline material arranged within an amorphous matrix, the first layer being arranged on the surface of the silicon substrate; a second layer comprising a percentage of crystalline material arranged within an amorphous matrix, the second layer being interposed between the first layer and the surface of the silicon substrate; wherein the percentage of crystalline material in the first layer is greater than the percentage of crystalline material in the second layer.

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